

Abstract of the Disclosure

An object of the present invention is to provide a sophisticated and highly reliable high-frequency Si-MOS semiconductor device having high ESD resistance. In the semiconductor device according to the present invention, lateral polysilicon diodes are formed and connected between high-frequency I/O signal line and the external supply voltage VDD, and between the ground GND and the high-frequency I/O signal line respectively. The forward direction of the diodes is the direction from the high-frequency I/O signal line to the VDD and the direction from the ground GND to the high-frequency I/O signal line respectively.

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